



**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

AB 1 B. 2004

**Docket Number (Optional)**  
**BUR92004001SUSI (17427)**

**Application Number**

**Applicant(s)**

Matthew J. Breitwisch, et al.

**Filing Date**

08/05/04

Group Art Unit

## Unassigned

## **U.S. PATENT DOCUMENTS**

## **FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
DWO	JP7007075A	10/1/95	Japan	-			

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

DWO		M.Q. Huda, et al., "Technique for Large Elevation of Source/Drain Using Implantation Mediated Selective Etching", <u>Electrochemical and Solid-State Letters</u> , pp. G117-G118 (2003).

**EXAMINER:** Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

IDS - 08/05/2004

**ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	ISOLATED FULLY DEPLETED SILICON-ON-INSULATOR REGIONS BY SELECTIVE ETCH						
<p>Application Number: Confirmation Number: First Named Applicant: Matthew Breitwisch Attorney Docket Number: BUR920040015US1 Search string: ( 5306659 or 5324683 or 5391911 or 6020250 or 6492705 ).pn.</p>							
<b>US Patent Documents</b>							
<p>Note: Applicant is not required to submit a paper copy of cited US Patent Documents</p>							
init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
DWO	1	5306659	1994-04-26	Beyer et al			
DWO	2	5324683	1994-06-08	Fitch et al			
DWO	3	5391911	1995-02-21	Beyer et al			
DWO	4	6020250	2000-02-01	Kenny			
DWO	5	6492705	2002-12-10	Begley et al			

Signature

Examiner Name	Date
/Douglas W Owens/	09/06/2006